AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 13, line 24 and bridging to page 14, line 22, with the following amended paragraph:

After these series of processes for doping an impurity, the annealing is performed for 30 seconds and at a temperature of 950 °C and in a hydrogen atmosphere with 5% of vapor added thereto. This annealing is intended for electrically activating the implanted impurity on the silicon substrate. If this annealing is performed in a nitrogen atmosphere, the hydrogen contained in a silicon nitride film formed on the side wall of the gate electrode causes boron to be likely leaked from the gate electrode into the substrate. After forming the source and drain of the MOS transistor, the thin silicon oxide film formed on the surface of the silicon substrate is removed by the hydrofluoric acid system etchant. In succession, Co is deposited to a thickness of 8 nm by means of the sputtering device. On the layer of Co is deposited TiNx having a depth of 20 nm. In this state, the annealing is performed at a temperature of 550 °C and in a nitrogen atmosphere. Then, with a mixture of sulfuric acid and hydrogen peroxide, the layer of TiN and the layer of Co that is not reactive with the silicon of the substrate are removed by the wet etching method. This annealing causes ~~a CO silicide~~ a Co silicide 19 to be left only on the per-ion-implanted surface of the silicon substrate for the purpose of self-adjustment. Further, the annealing at a temperature of 850 °C and in a nitrogen atmosphere causes the Co silicide to be low in resistance.